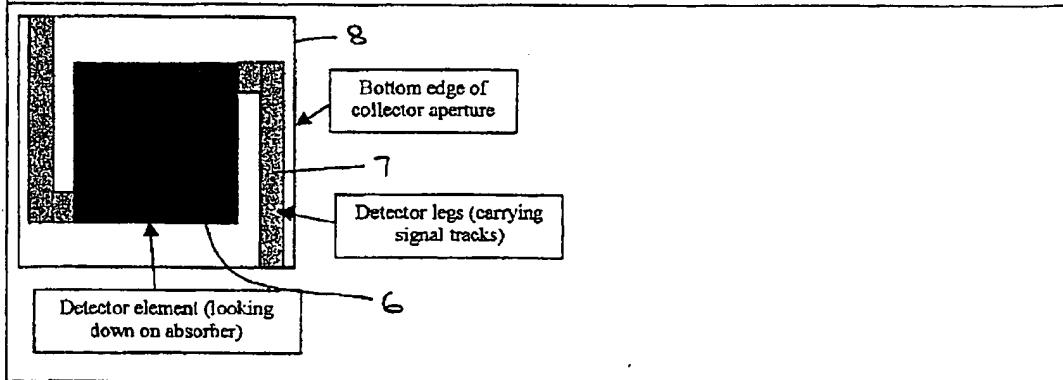
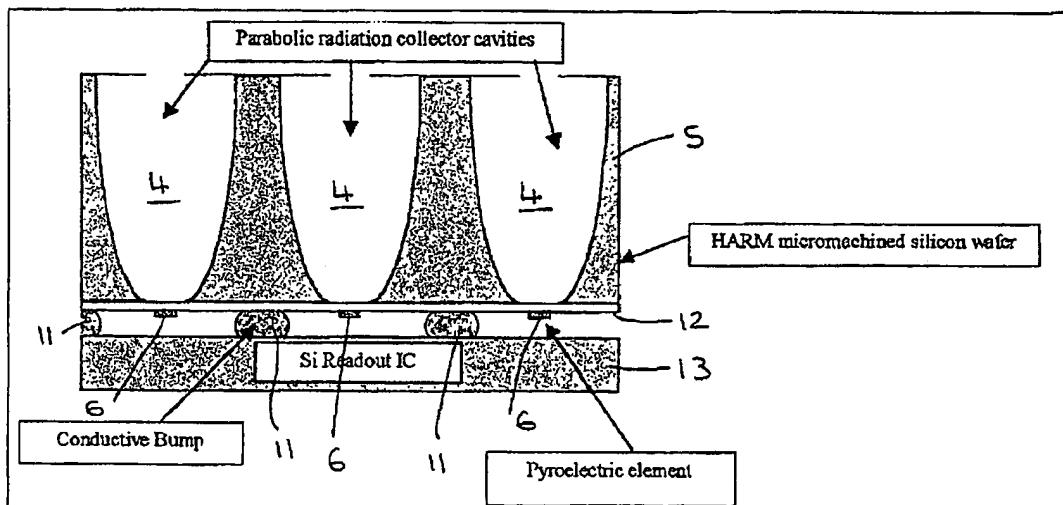
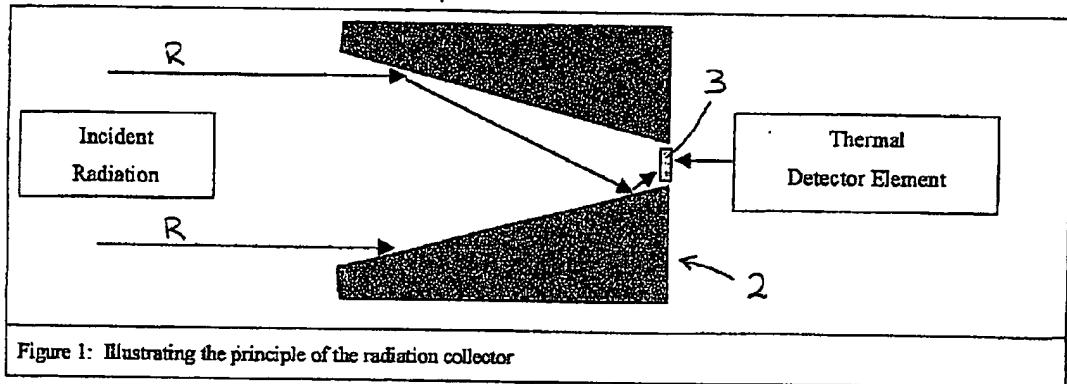
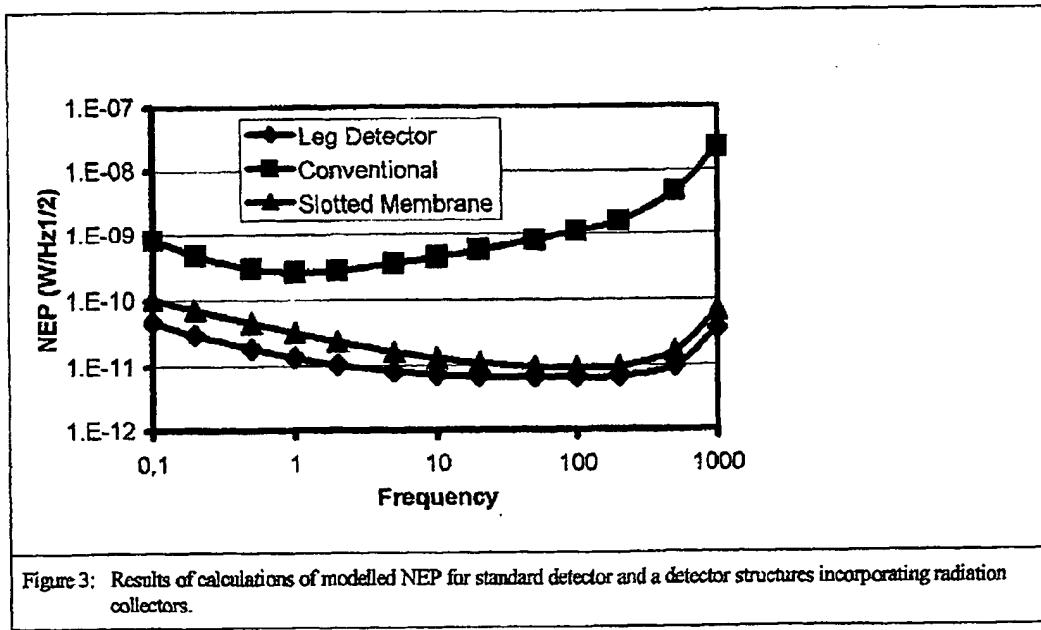
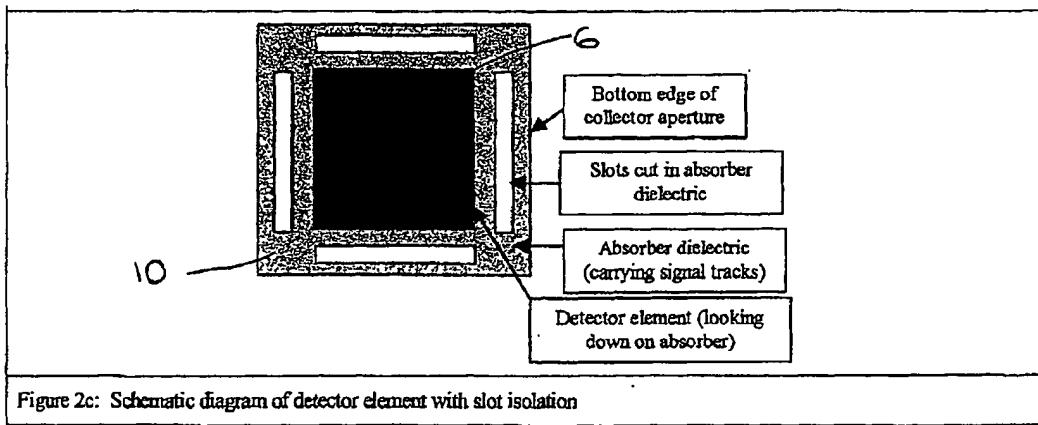


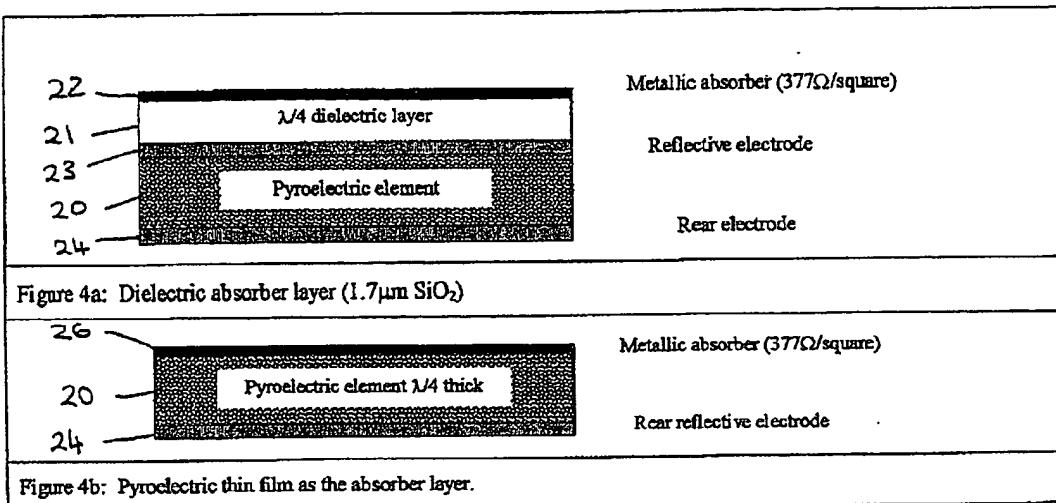
1/6



2/6



3/6



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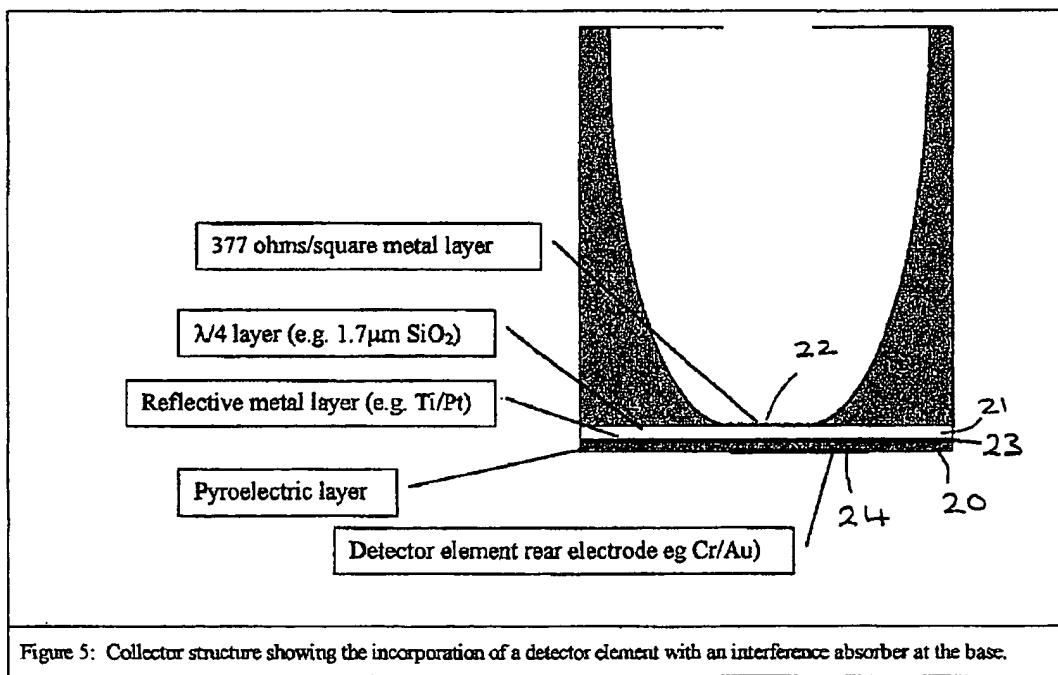


Figure 5: Collector structure showing the incorporation of a detector element with an interference absorber at the base.

4/6

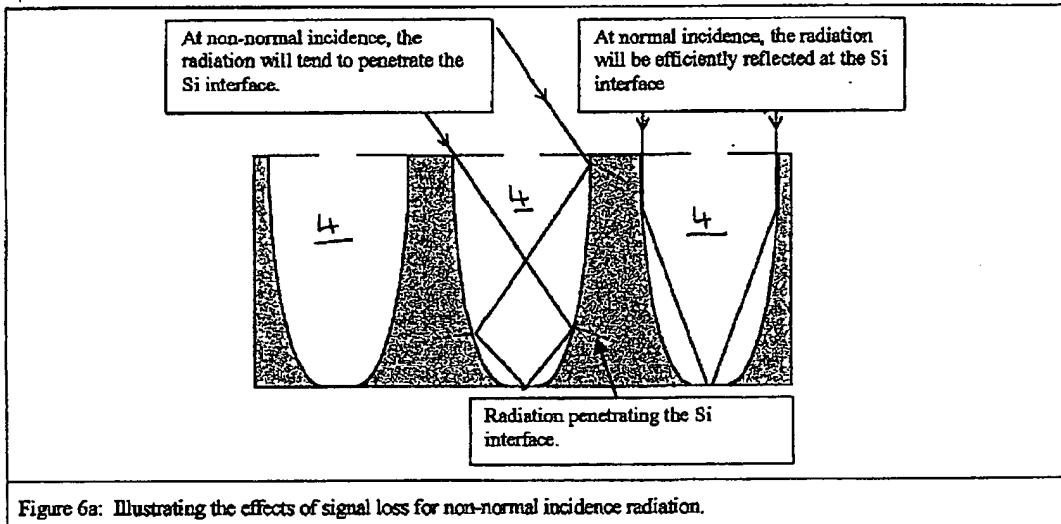


Figure 6a: Illustrating the effects of signal loss for non-normal incidence radiation.

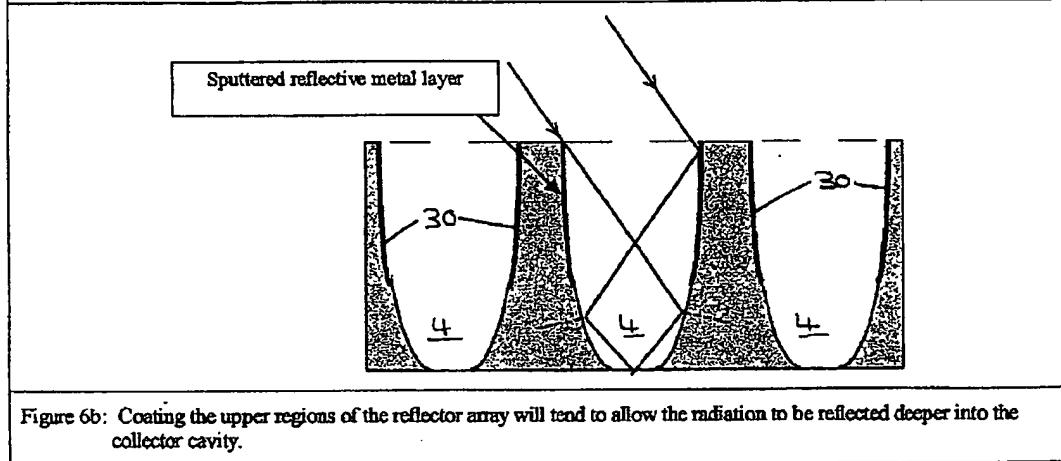


Figure 6b: Coating the upper regions of the reflector array will tend to allow the radiation to be reflected deeper into the collector cavity.

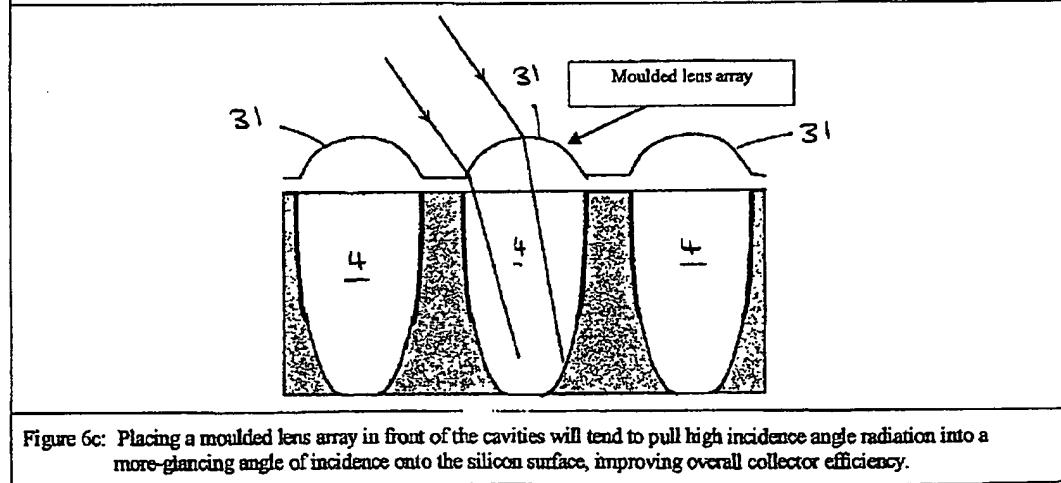


Figure 6c: Placing a moulded lens array in front of the cavities will tend to pull high incidence angle radiation into a more-glancing angle of incidence onto the silicon surface, improving overall collector efficiency.

5/6

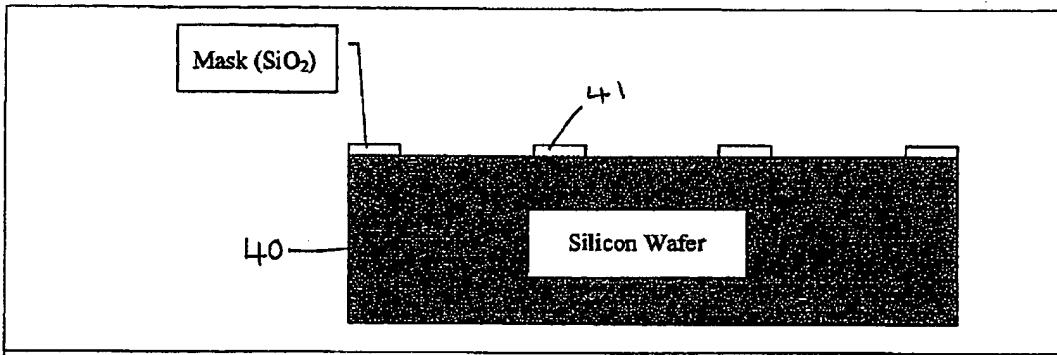


Figure 7a: Silicon wafer with "hard" mask defined

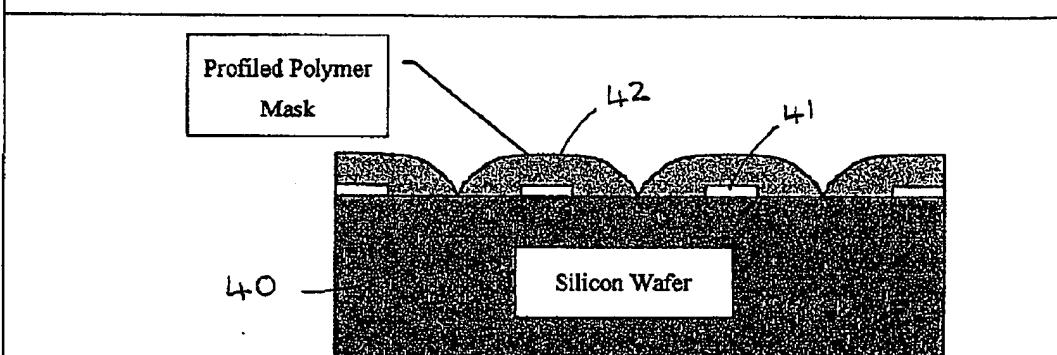


Figure 7b: Silicon wafer with profiled polymer mask defined

6/6

